SS025N10TS N-MOSFET 100V, 210A, 2.1mΩ

Description

SS025N10TS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
VDSS	100	V
П	210	Α
R DS(on).typ	2.1	mΩ

FEATURES:

- Fast Switching
- Low On-Resistance (RDS(on)≤2.5mΩ)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

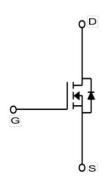
APPLICATIONS:

- Switching applications
- Motor drivers
- BMS
- Synchronous rectification

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS025N10TS	TO-220	SS025N10TS	TUBE

Schematic Diagram



TO-220

